



STFI260N6F6

N-channel 60 V, 0.0024 Ω , 80 A STripFET™ VI DeepGATE™
Power MOSFET in I²PAKFP package

Datasheet — preliminary data

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D
STFI260N6F6	60 V	< 0.003 Ω	80 A

- Fully insulated and low profile package with increased creepage path from pin to heatsink plate
- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Application

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

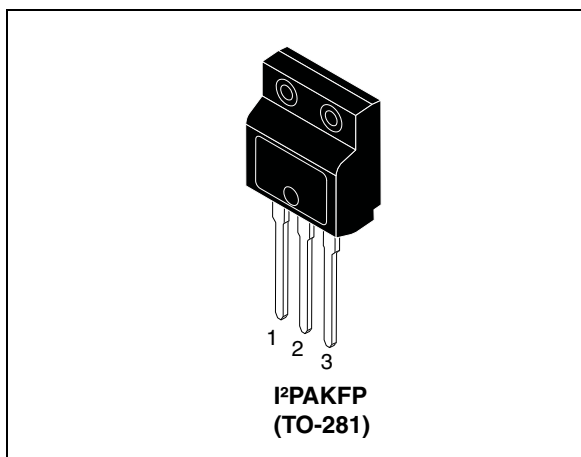


Figure 1. Internal schematic diagram

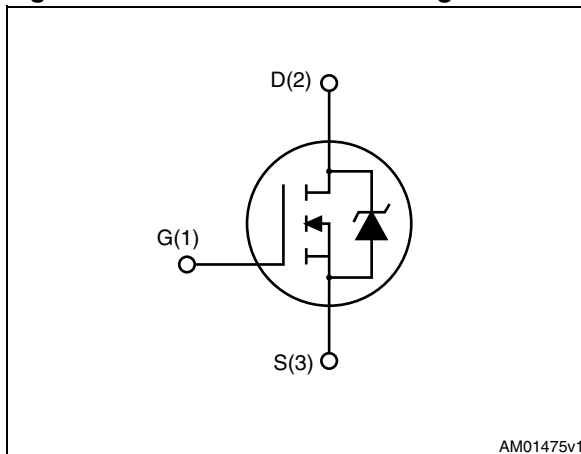


Table 1. Device summary

Order codes	Marking	Package	Packaging
STFI260N6F6	260N6F6	I ² PAK (TO-281)	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80 ⁽¹⁾	A
$I_{DM}^{(1)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	41.7	W
	Derating factor	0.28	W/ $^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	3.6	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu\text{A}$	60			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = 60\ \text{V}$ $V_{DS} = 60\ \text{V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}, I_D = 60\ \text{A}$		2.4	3	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			11400		pF
C_{oss}	Output capacitance	$V_{DS} = 25\ \text{V}, f = 1\ \text{MHz},$ $V_{GS} = 0$	-	1100	-	pF
C_{rss}	Reverse transfer capacitance			400		pF
Q_g	Total gate charge	$V_{DD} = 30\ \text{V}, I_D = 120\ \text{A},$ $V_{GS} = 10\ \text{V}$ <i>(see Figure 14)</i>		183		nC
Q_{gs}	Gate-source charge		-	53	-	nC
Q_{gd}	Gate-drain charge			41		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\ \text{V}, I_D = 60\ \text{A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\ \text{V}$ <i>(see Figure 13)</i>	-	31.4	-	ns
t_r	Rise time		-	165	-	ns
$t_{d(off)}$	Turn-off-delay time		-	144.4	-	ns
t_f	Fall time			62.6		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120\text{ A}, V_{GS} = 0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 120\text{ A}, V_{DD} = 48\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	55.6		ns
Q_{rr}	Reverse recovery charge			116		nC
I_{RRM}	Reverse recovery current			3.8		A

1. Current limited by package.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

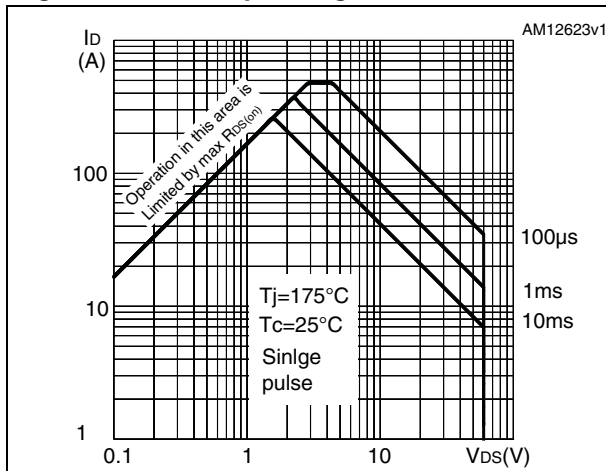


Figure 3. Thermal impedance

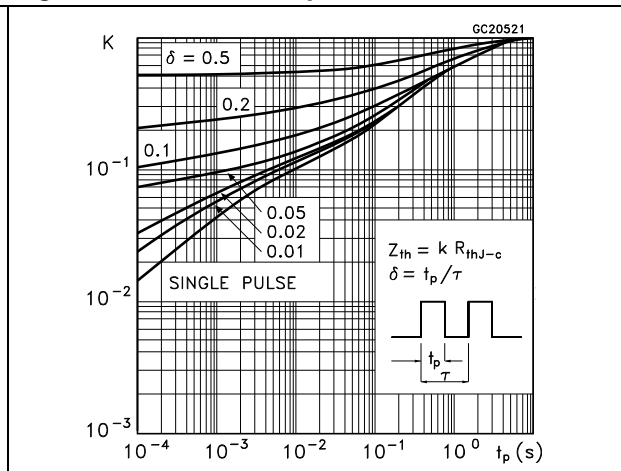


Figure 4. Output characteristics

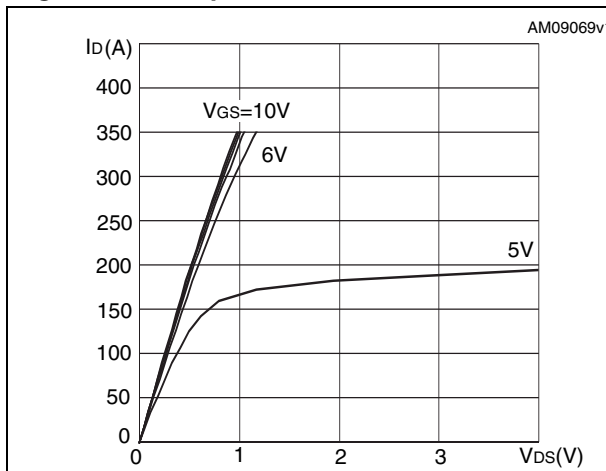


Figure 5. Transfer characteristics

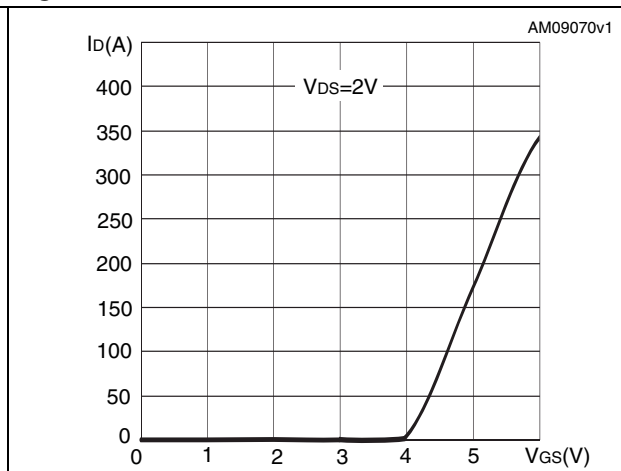


Figure 6. Normalized $B_{V_{DS}}$ vs. temperature

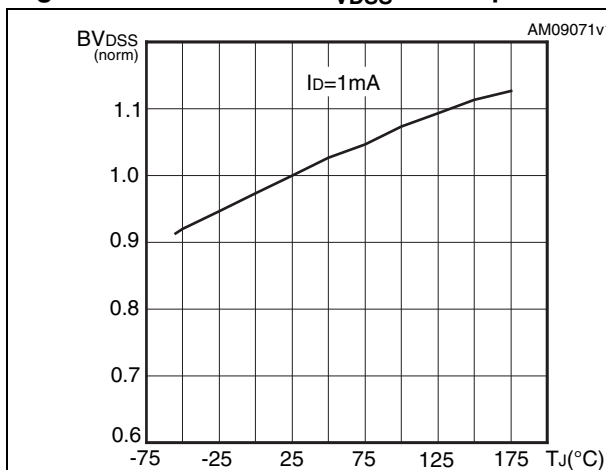


Figure 7. Static drain-source on-resistance

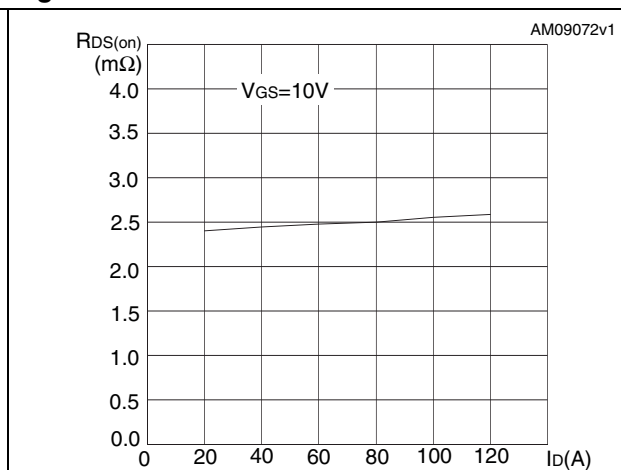


Figure 8. Gate charge vs. gate-source voltage

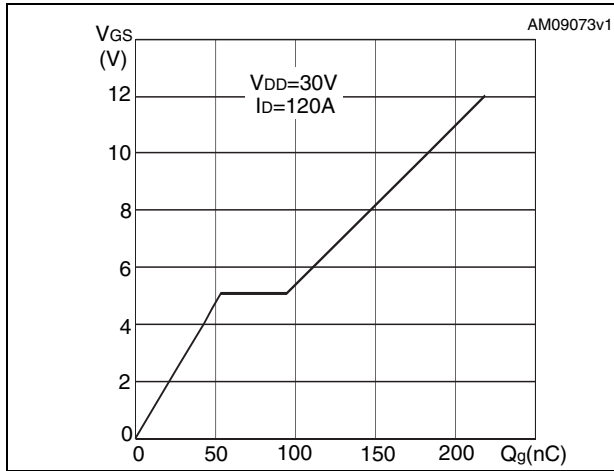


Figure 9. Capacitance variations

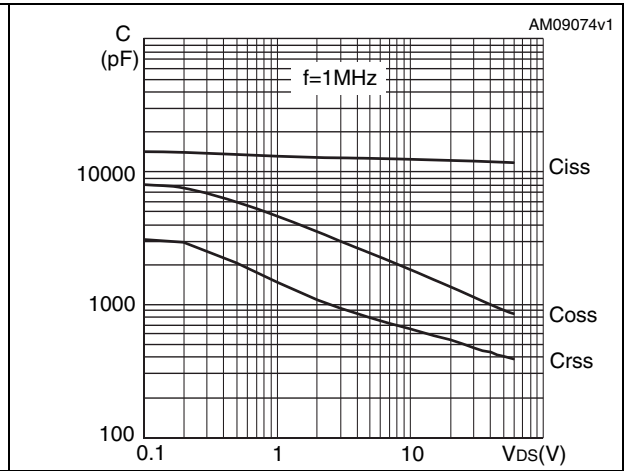


Figure 10. Normalized gate threshold voltage vs. temperature

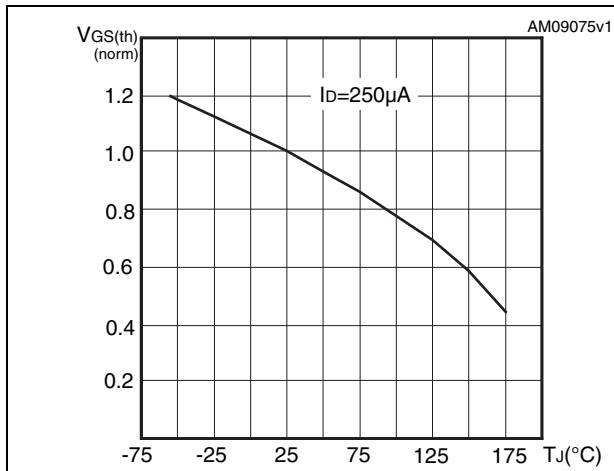


Figure 11. Normalized on-resistance vs. temperature

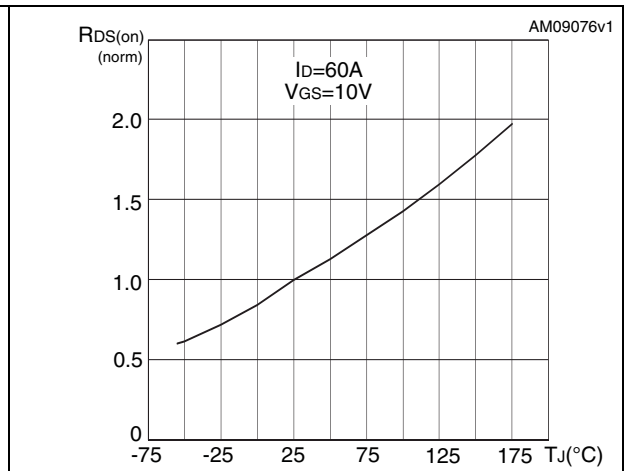
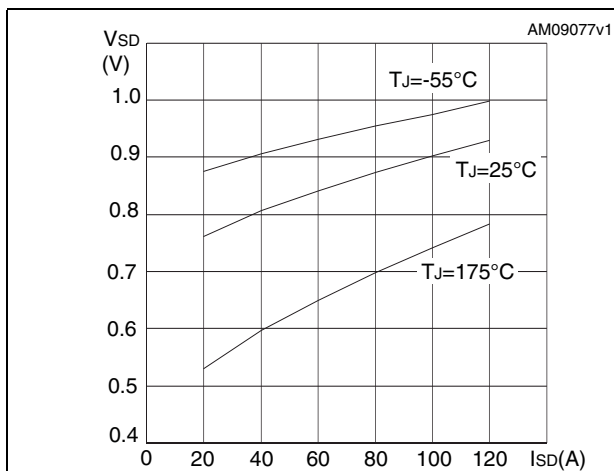
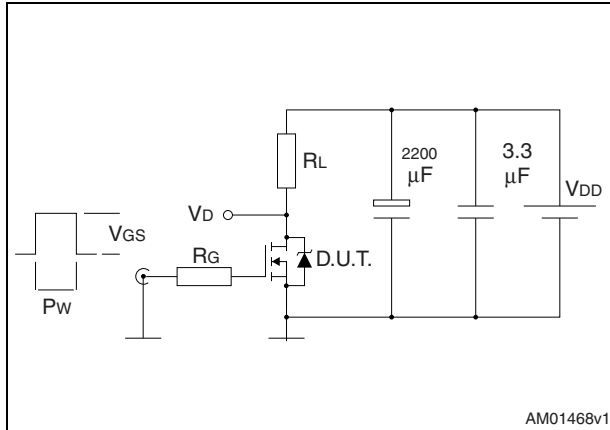


Figure 12. Source-drain diode forward characteristics



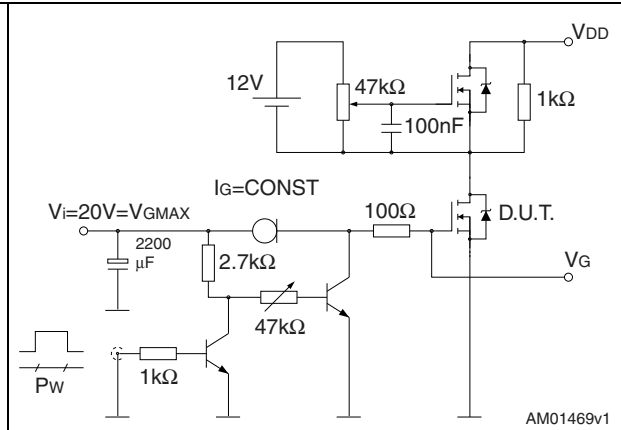
3 Test circuits

Figure 13. Switching times test circuit for resistive load



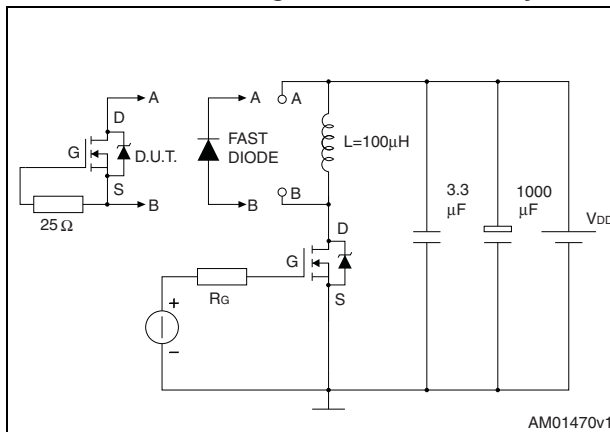
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Figure 14. Gate charge test circuit



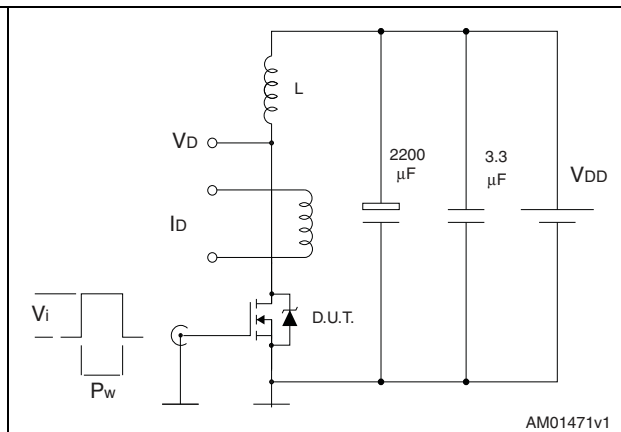
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Figure 15. Test circuit for inductive load switching and diode recovery times



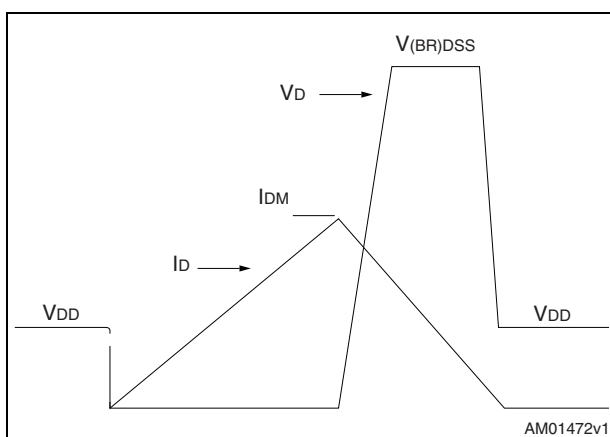
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Figure 16. Unclamped inductive load test circuit



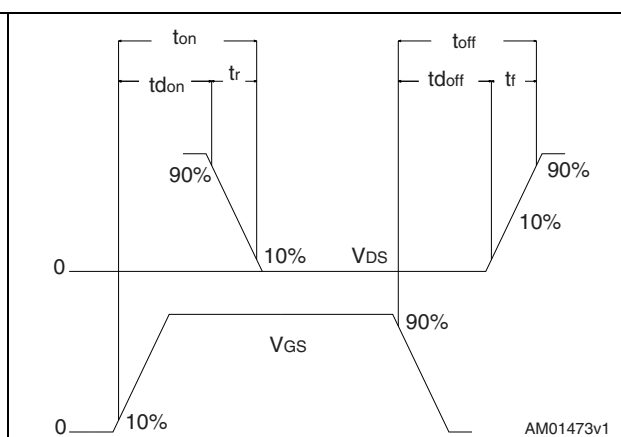
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

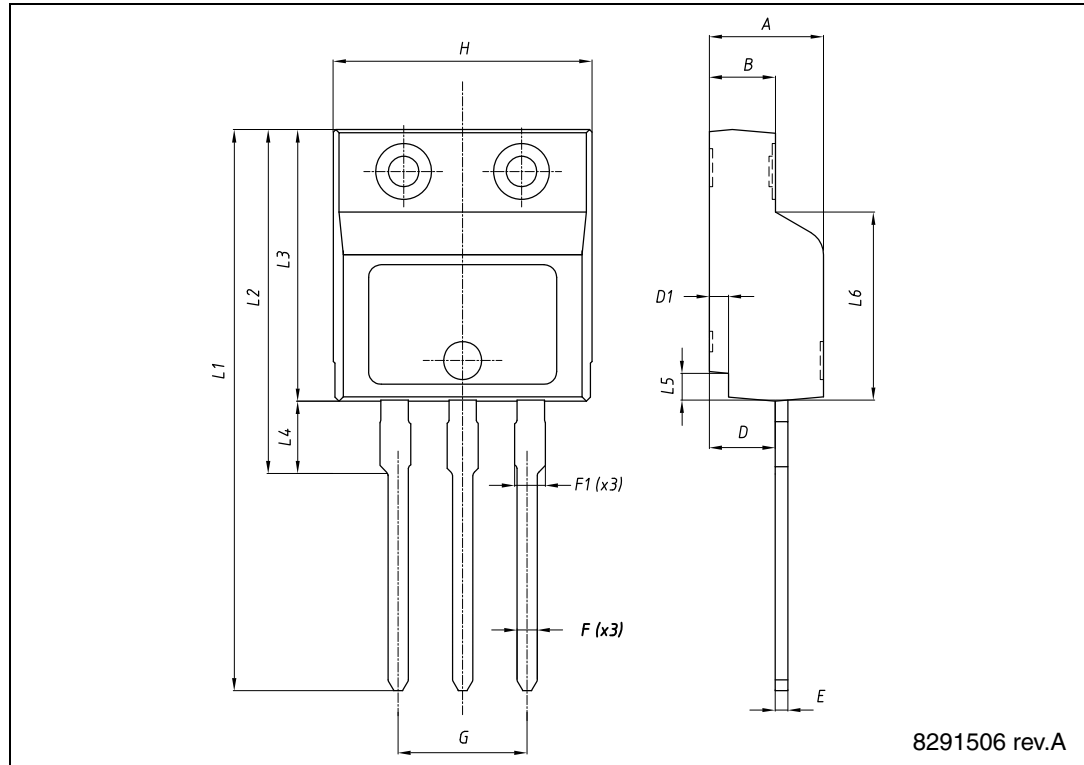
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. I²PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 19. I²PAKFP (TO-281) drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
13-Apr-2012	1	First release.

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